

isc Silicon NPN Darlington Power Transistor

2SD864

DESCRIPTION

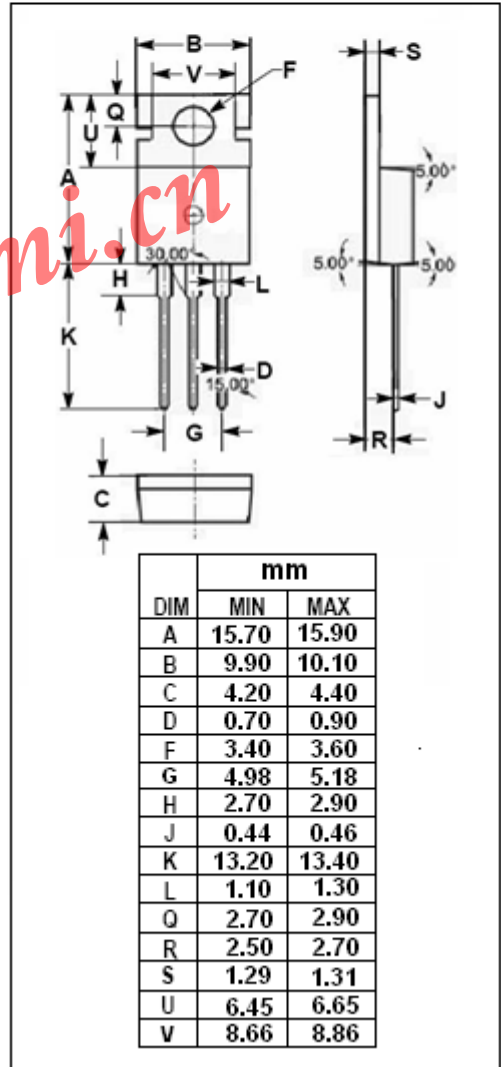
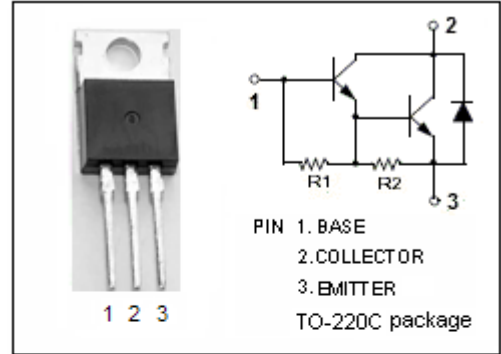
- High DC Current Gain-
: $h_{FE} = 1000(\text{Min}) @ I_C = 1.5\text{A}$
- Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = 120\text{V}(\text{Min})$
- Low Collector-Emitter Saturation Voltage-
: $V_{CE(\text{sat})} = 1.5\text{V}(\text{Max}) @ I_C = 1.5\text{A}$
- Complement to Type 2SB765

APPLICATIONS

- Medium speed and power switching applications.

ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	120	V
V_{CEO}	Collector-Emitter Voltage	120	V
V_{EBO}	Emitter-Base Voltage	7	V
I_C	Collector Current-Continuous	3	A
I_{CM}	Collector Current-Peak	6	A
P_C	Collector Power Dissipation $T_C = 25^\circ\text{C}$	30	W
T_j	Junction Temperature	150	°C
T_{stg}	Storage Temperature Range	-55~150	°C



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ELECTRICAL CHARACTERISTICS

 $T_C=25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C=25\text{mA}$, $R_{BE}=\infty$	120			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E=50\text{mA}$, $I_C=0$	7			V
$V_{CE(sat)-1}$	Collector-Emitter Saturation Voltage	$I_C=1.5\text{A}$, $I_B=-3\text{mA}$			1.5	V
$V_{CE(sat)-2}$	Collector-Emitter Saturation Voltage	$I_C=3\text{A}$, $I_B=-30\text{mA}$			3.0	V
$V_{BE(sat)-1}$	Base-Emitter Saturation Voltage	$I_C=1.5\text{A}$, $I_B=-3\text{mA}$			2.0	V
$V_{BE(sat)-2}$	Base-Emitter Saturation Voltage	$I_C=3\text{A}$, $I_B=-30\text{mA}$			3.5	V
I_{CBO}	Collector Cutoff Current	$V_{CB}=120\text{V}$, $I_E=0$			100	μA
I_{CEO}	Collector Cutoff Current	$V_{CE}=100\text{V}$, $R_{BE}=\infty$			10	μA
h_{FE}	DC Current Gain	$I_C=1.5\text{A}$; $V_{CE}=3\text{V}$	1000		20000	

Switching times

t_{on}	Turn-on Time	$I_C=1.5\text{A}$; $I_{B1}=-I_{B2}=3\text{mA}$		0.5		μs
t_{stg}	Storage Time			4.5		μs
t_f	Fall Time			1.1		μs